

8.0A 4Quadrants TRIACs

Product Summary

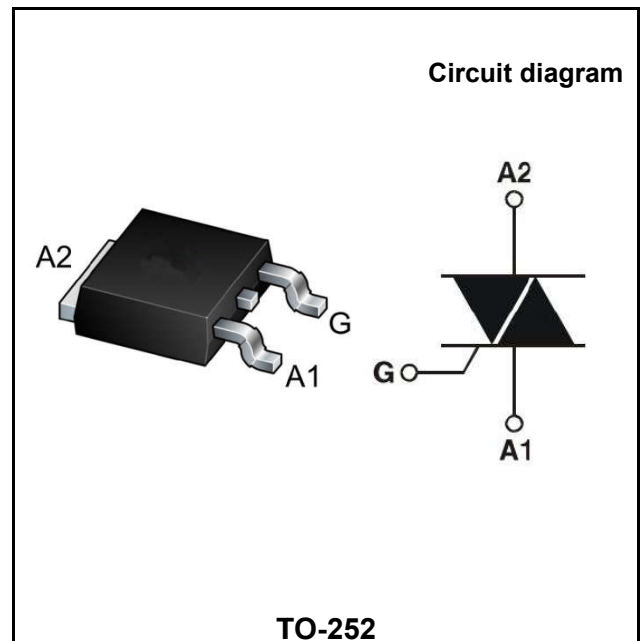
Symbol	Value	Unit
$I_{T(RMS)}$	8.0	A
$V_{DRM} V_{RRM}$	600/800	V
V_{TM}	1.55	V

Features

With high ability to withstand the shock loading of large current, With high commutation performances, 4 quadrants products especially recommended for use on inductive load.

Application

Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.



Order Information

Part Number	Package	Marking	Delivery Form	Delivery Quantity
BT137D	TO-252	BT137 800E XXXX	12" T&R	2500PCS/Tape

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600/800	V
Repetitive peak reverse voltage	V_{RRM}	600/800	V
RMS on-state current	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	65	A
i^2t value for fusing (tp=10ms)	i^2t	21	A ² s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di_T/dt	I - II - III	50
		IV	10
Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_G (AV)$	0.5	W
Junction Temperature	T_J	-40~+125	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value		Unit	
			Min	Max		
Gate trigger current	I _{GT}	V _D =12V I _T =0.1A T _j =25°C	I - II - III	-	10	mA
			IV	-	25	
Gate trigger voltage	V _{GT}	I - II - III - IV	-	1.5	V	
Gate non-trigger voltage	V _{GD}	V _D = V _{DRM} T _j = 125°C	0.2	-	V	
latching current	I _L	V _D = 12V I _{GT} = 0.1A T _j = 25°C	I - III - IV	-	25	mA
			II	-	35	
Holding current	I _H	I - II - III - IV	-	20	mA	
Critical-rate of rise of commutation voltage	dV _D /dt	V _D = 2/3 V _{DRM} Gate Open T _j = 125°C	20	-	V/us	

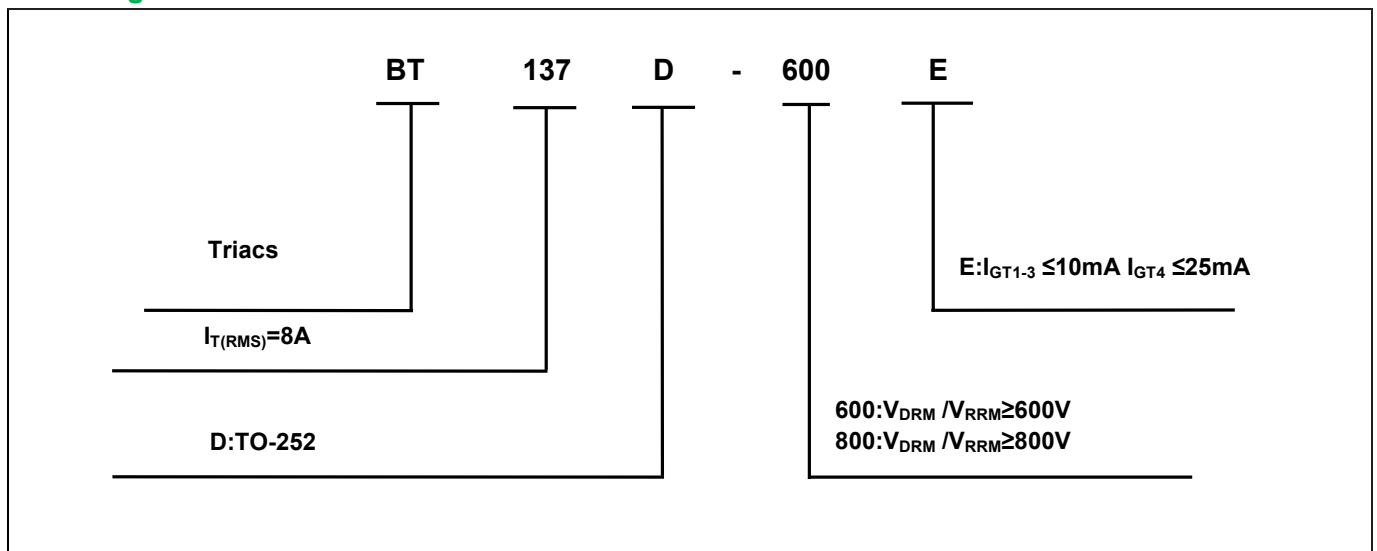
STATIC CHARACTERISTICS

Forward "on" voltage	V _{TM}	I _{TM} = 10A tp = 380µs	-	1.55	V	
Repetitive Peak Off-State Current	I _{DRM}	V _D = V _{DRM} V _R = V _{RRM}	T _j = 25°C	-	5	µA
Repetitive Peak Reverse Current	I _{RRM}		T _j = 125°C	-	1	mA

THERMAL RESISTANCES

Thermal resistance	R _{th(j-c)}	Junction to case(AC)	TYP.	1.6	°C/W
	R _{th(j-a)}	Junction to ambient	TYP.	70	°C/W

Ordering Information



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

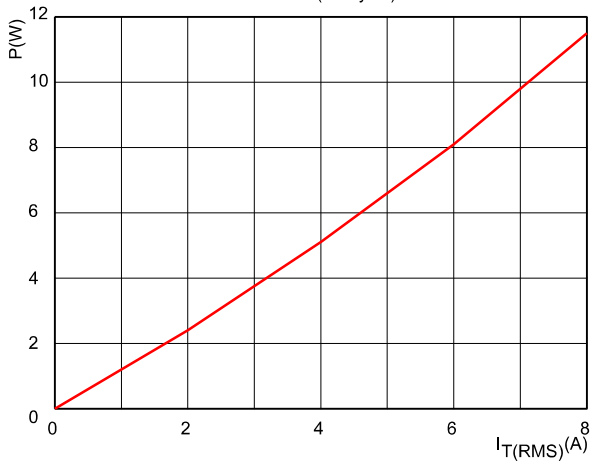


FIG.2: RMS on-state current versus case temperature (full cycle)

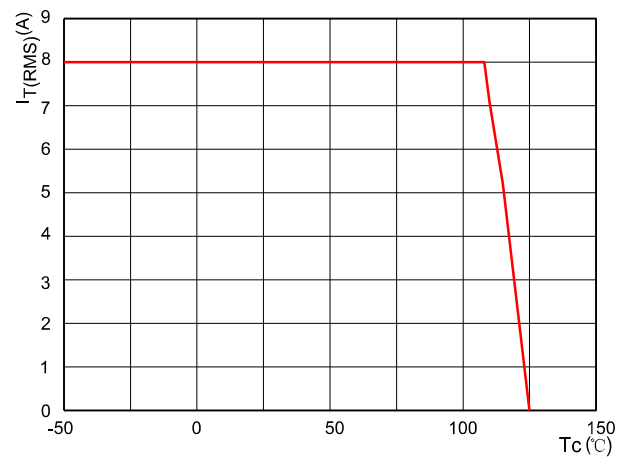


FIG.3: Surge peak on-state current versus number of cycles

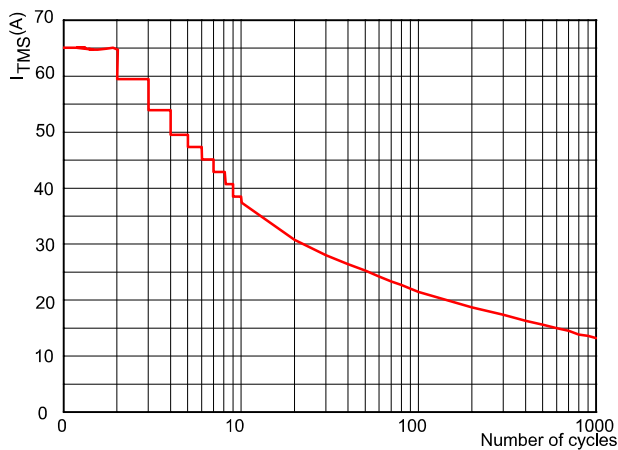


FIG.4: On-state characteristics (maximum values)

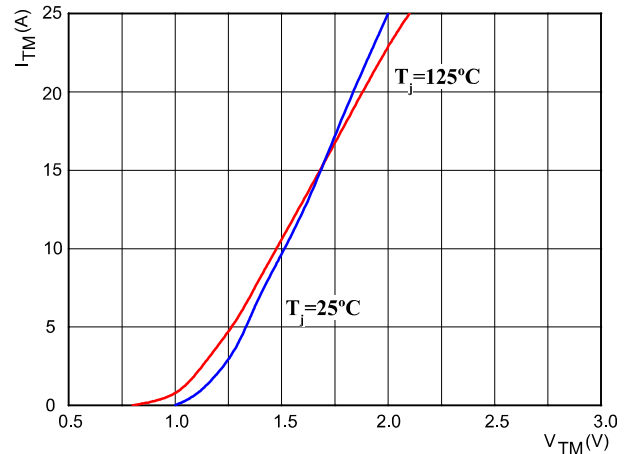


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

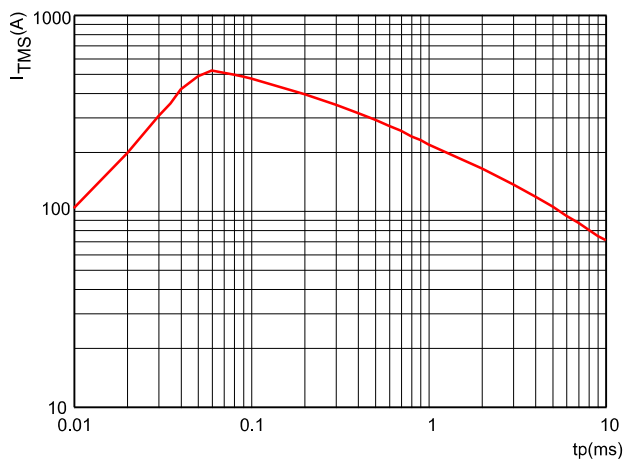
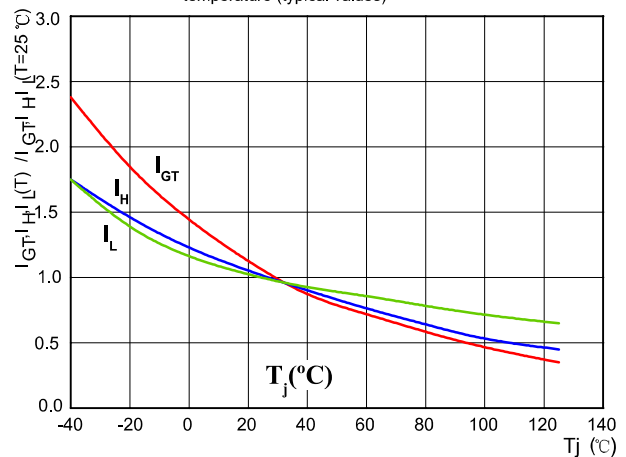


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Package Information

TO-252

